Ordering number : ENN7004

P-Channel Silicon MOSFET

FTS1012

Load Switching Applications

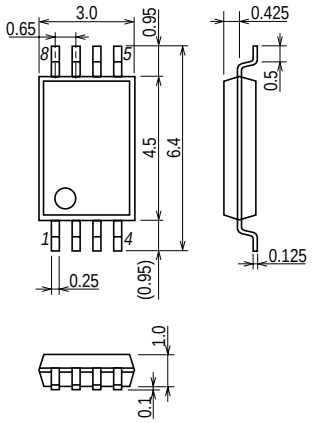
Features

- Low ON-resistance.
- 4.0V drive.
- Mounting height 1.1mm.

Package Dimensions

unit : mm
2147A

[FTS1012]



1 : Drain
2 : Source
3 : Source
4 : Gate
5 : Drain
6 : Source
7 : Source
8 : Drain

SANYO : TSSOP8

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		-30	V
Gate-to-Source Voltage	V_{GSS}		±20	V
Drain Current (DC)	I_D		-6	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	-32	A
Allowable Power Dissipation	P_D	Mounted on a ceramic board (1000mm²×0.8mm)	1.3	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=-1mA, V_{GS}=0	-30			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=-30V, V_{GS}=0			-1	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±16V, V_{DS}=0			±10	μA
Cutoff Voltage	$V_{GS}(off)$	V_{DS}=-10V, I_D=-1mA	-1.0		-2.4	V
Forward Transfer Admittance	$\|yfs\|$	V_{DS}=-10V, I_D=-6A	8.7	12		S

Marking : S1012

Continued on next page.

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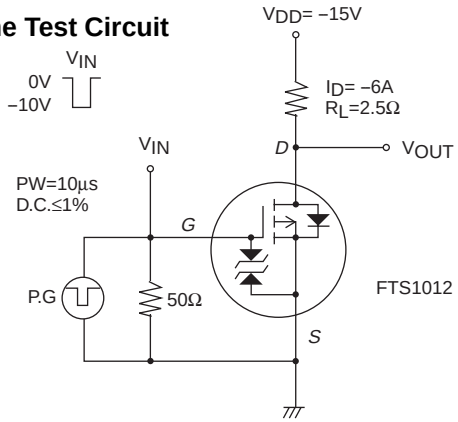
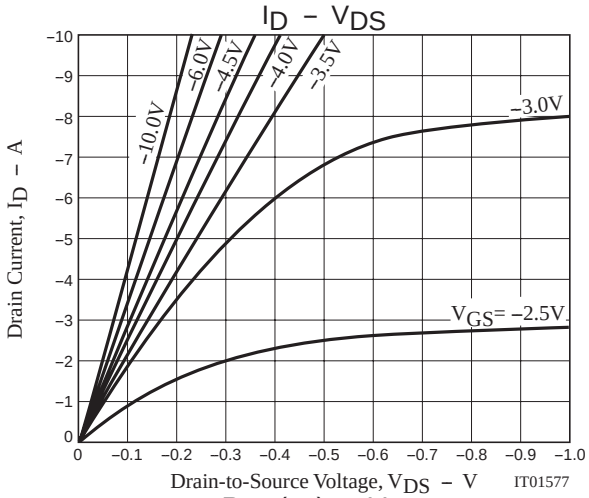
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

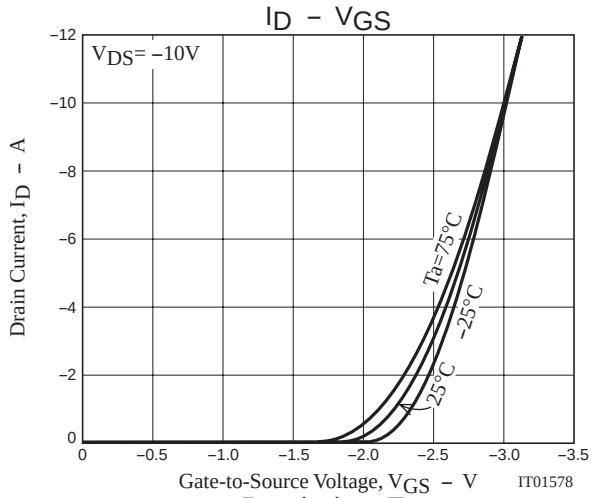
Continued from preceding page.

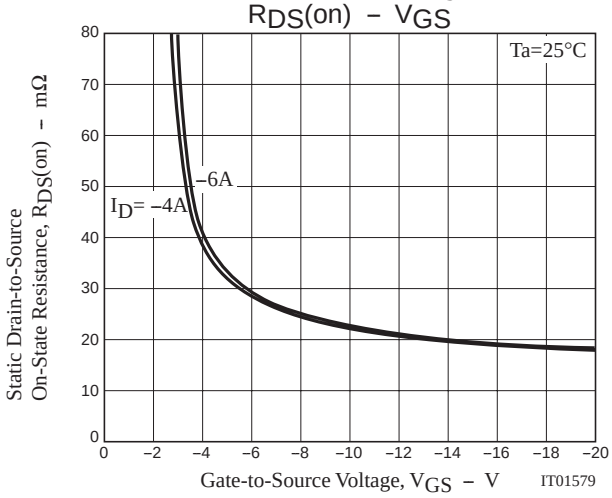
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Static Drain-to-Source On-State Resistance	R_{DS}(on) 1	I_D=-6A, V_{GS}=-10V		21	28	mΩ
	R_{DS}(on) 2	I_D=-4A, V_{GS}=-4.5V		33	47	mΩ
	R_{DS}(on) 3	I_D=-4A, V_{GS}=-4V		37	52	mΩ
Input Capacitance	Ciss	V_{DS}=-10V, f=1MHz		1700		pF
Output Capacitance	Coss	V_{DS}=-10V, f=1MHz		380		pF
Reverse Transfer Capacitance	Crss	V_{DS}=-10V, f=1MHz		240		pF
Turn-ON Delay Time	t_d(on)	See specified Test Circuit		15		ns
Rise Time	t_r	See specified Test Circuit		130		ns
Turn-OFF Delay Time	t_d(off)	See specified Test Circuit		110		ns
Fall Time	t_f	See specified Test Circuit		85		ns
Total Gate Charge	Qg	V_{DS}=-10V, V_{GS}=-10V, I_D=-6A		32		nC
Gate-to-Source Charge	Qgs	V_{DS}=-10V, V_{GS}=-10V, I_D=-6A		4.5		nC
Gate-to-Drain “Miller” Charge	Qgd	V_{DS}=-10V, V_{GS}=-10V, I_D=-6A		5		nC
Diode Forward Voltage	V_{SD}	I_S=-6A, V_{GS}=0		-0.79	-1.5	V

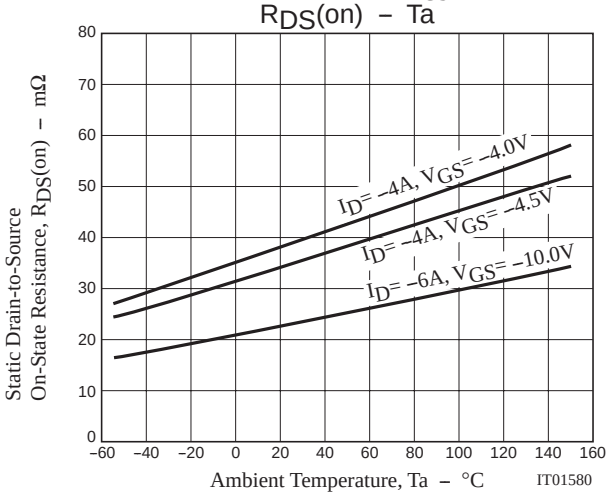
Switching Time Test Circuit

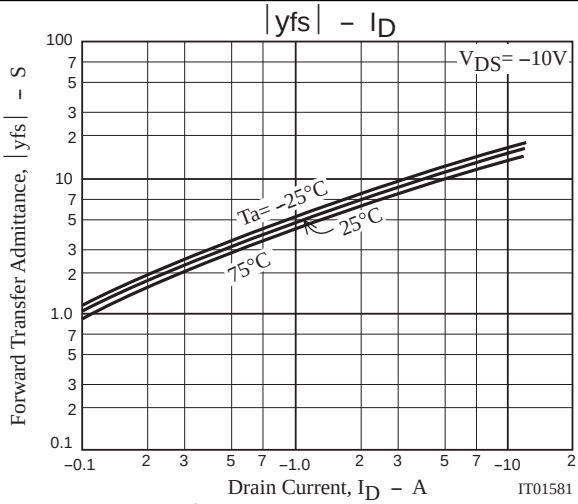


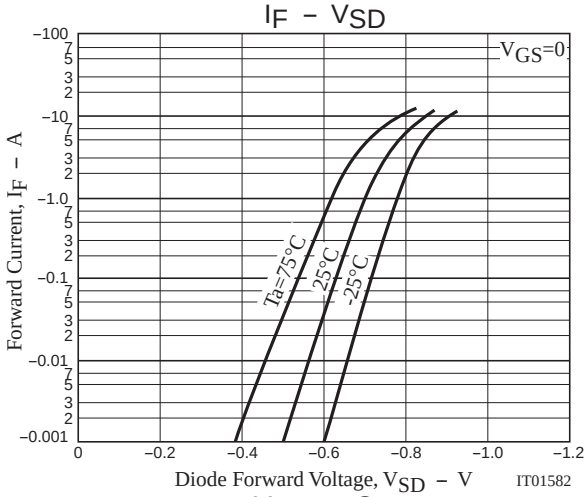


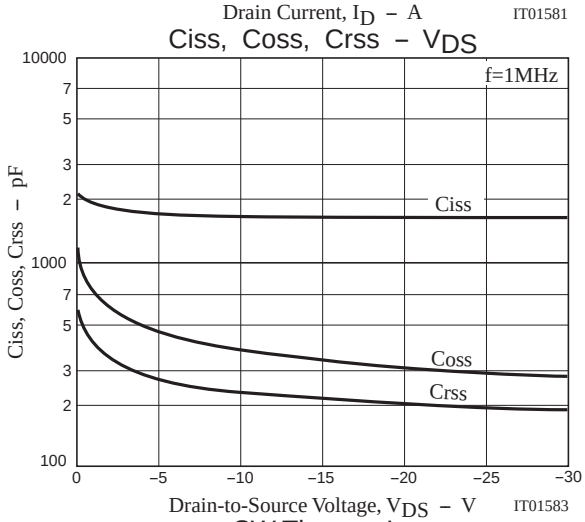


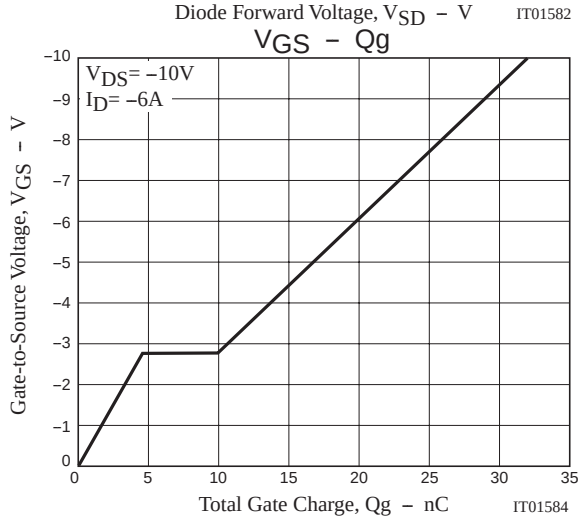


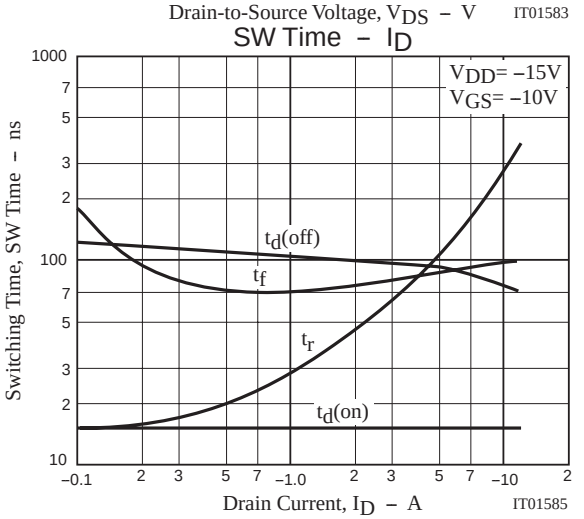


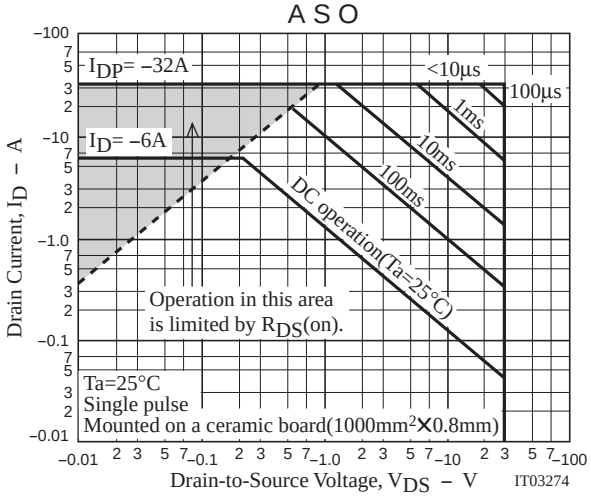

|yfs| – ID
VDS= –10V
Ta= –25°C
25°C
75°C
Forward Transfer Admittance, |yfs| – S
Drain Current, ID – A
IT01581

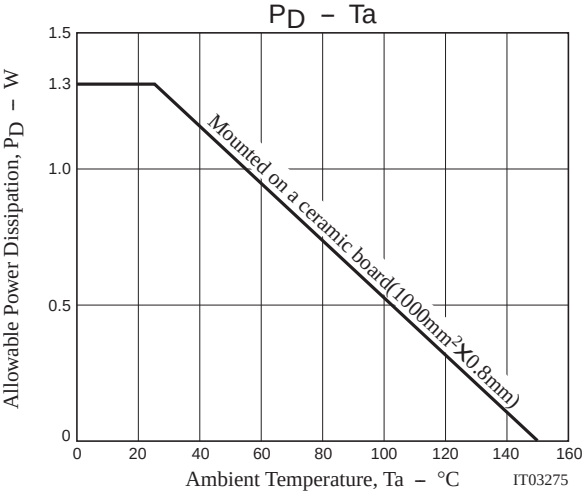

IF – VSD
VGS=0
Ta=75°C
25°C
–25°C
Forward Current, IF – A
Diode Forward Voltage, VSD – V
IT01582


Ciss, Coss, Crss – VDS
f=1MHz
Ciss
Coss
Crss
Ciss, Coss, Crss – pF
Drain-to-Source Voltage, VDS – V
IT01583


VGS – Qg
VDS= –10V
ID= –6A
Gate-to-Source Voltage, VGS – V
Total Gate Charge, Qg – nC
IT01584


SW Time – ID
VDD= –15V
VGS= –10V
td(off)
tf
tr
td(on)
Switching Time, SW Time – ns
Drain Current, ID – A
IT01585


A S O
IDP= –32A
ID= –6A
<10µs
100µs
1ms
10ms
100ms
DC operation(Ta=25°C)
Operation in this area
is limited by RDS(on).
Ta=25°C
Single pulse
Mounted on a ceramic board(1000mm2×0.8mm)
Drain Current, ID – A
Drain-to-Source Voltage, VDS – V
IT03274


PD – Ta
Mounted on a ceramic board(1000mm2×0.8mm)
Allowable Power Dissipation, PD – W
Ambient Temperature, Ta – °C
IT03275

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